N-Channel Silicon MOSFET

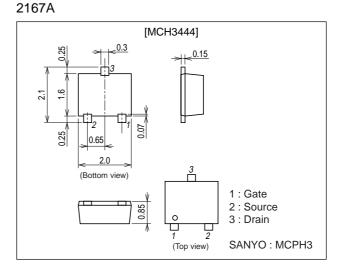


Features

- · Low ON-resinstance.
- · Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	۱ _D		2.5	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	10	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.3A	1.9	3.2		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=1.3A, VGS=4V		82	108	mΩ
	RDS(on)2	ID=0.7A, VGS=2.5V		105	150	mΩ
Marking : ZV Continued on next pa						

Marking : ZV

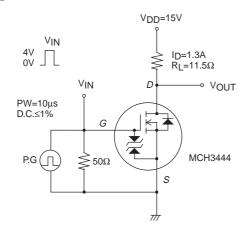
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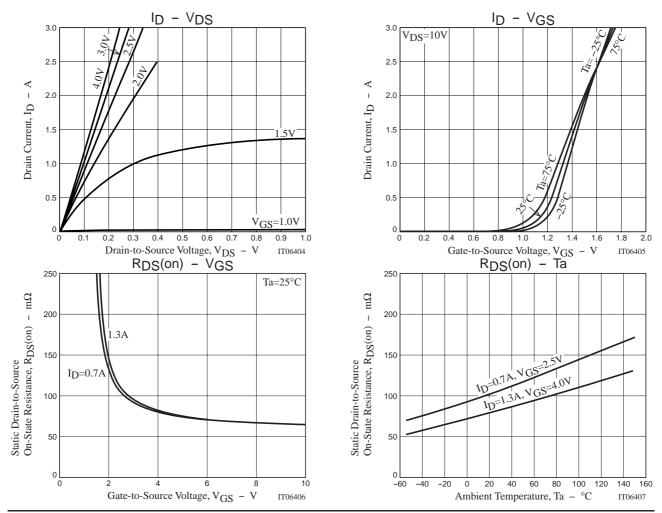
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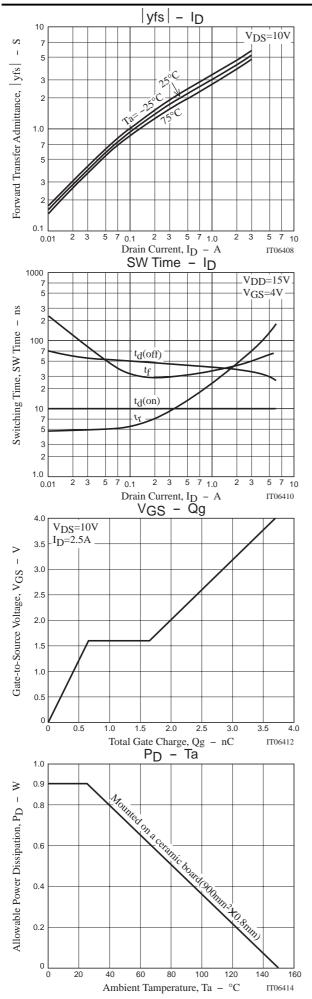
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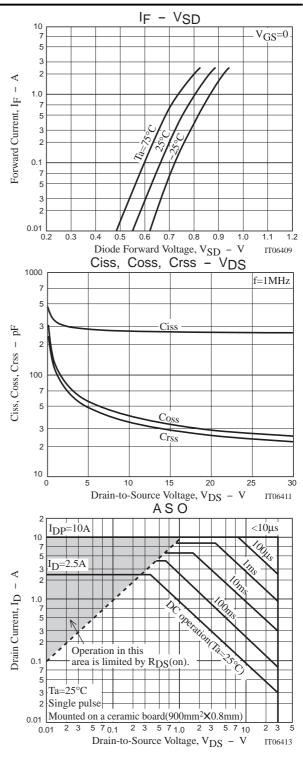
Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		270		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		40		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		35		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		10		ns
Rise Time	tr	See specified Test Circuit.		40		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		39		ns
Fall Time	tf	See specified Test Circuit.		38		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4V, I _D =2.5A		3.7		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4V, I _D =2.5A		0.65		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4V, I _D =2.5A		1.0		nC
Diode Forward Voltage	V _{SD}	IS=2.5A, VGS=0		0.9	1.2	V

Switching Time Test Circuit









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